

ABSTRACT

An exposure method is disclosed, in which a surface of a wafer can be conformed to an image plane highly accurately even when an angle of inclination of a running surface of a wafer stage is varied when a pattern for a semiconductor device or the like is transferred onto the wafer in accordance with the scanning exposure system. The focusing is performed in an exposure area on the basis of a focus position detected in a pre-reading area in which the focus position can be detected highly accurately although the detection range is narrow, disposed in front of the exposure area on the wafer in the scanning direction. In order to allow the surface of the wafer to be included in the detection range of the focus position in the pre-reading area, the focus position of the wafer is roughly conformed to the image plane on the basis of a result of detection at a rough detecting point for roughly detecting the focus position in front of the pre-reading area with a wide detection range.